

V_{DSS}	1700V
$R_{DS(on)}$ (Typ.)	1.15Ω
I_D	3.7A
P_D	35W

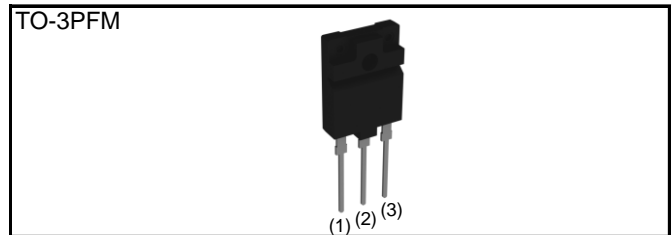
●Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Long creepage distance
- 4) Simple to drive
- 5) Pb-free lead plating ; RoHS compliant

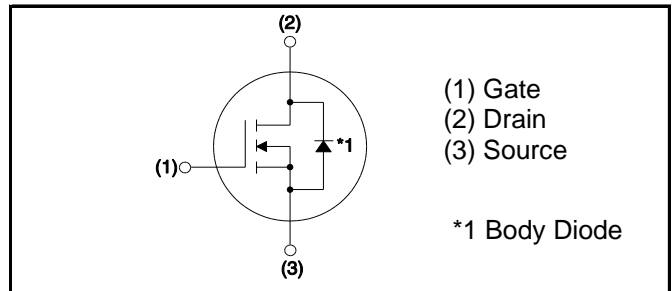
●Application

- Auxiliay power supplies
- Switch mode power supplies

●Outline



●Inner circuit



●Packaging specifications

Type	Packaging	Tube
	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	30
	Taping code	-
	Marking	SCT2H12NZ

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Value	Unit	
Drain - Source voltage	V_{DSS}	1700	V	
Continuous drain current	$T_c = 25^\circ\text{C}$	I_D^{*1}	3.7	A
	$T_c = 100^\circ\text{C}$	I_D^{*1}	2.6	A
Pulsed drain current	$I_{D,pulse}^{*2}$	9.2	A	
Gate - Source voltage (DC)	V_{GSS}	-6 to 22	V	
Gate - Source surge voltage ($T_{surge} < 300\text{nsec}$)	$V_{GSS-surge}^{*3}$	-10 to 26	V	
Power dissipation ($T_c = 25^\circ\text{C}$)	P_D	35	W	
Junction temperature	T_j	175	°C	
Range of storage temperature	T_{stg}	-55 to +175	°C	

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	R_{thJC}	-	3.32	4.32	°C/W
Thermal resistance, junction - ambient	R_{thJA}	-	36.8	50	°C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	°C

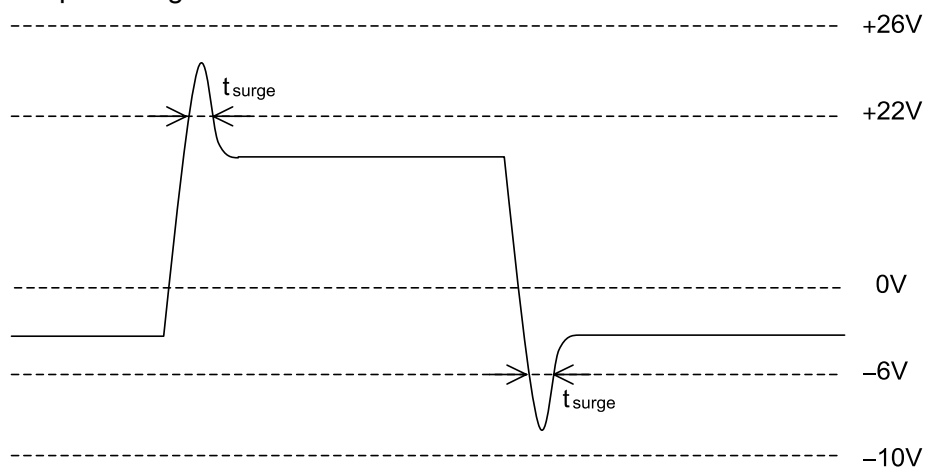
●Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	1700	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 1700V, V_{GS} = 0V$	-	0.1	10	μA
		$T_j = 150^\circ\text{C}$	-	0.2	-	
Gate - Source leakage current	I_{GSS+}	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I_{GSS-}	$V_{GS} = -6V, V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 0.9mA$	1.6	2.8	4.0	V

*1 Limited only by maximum temperature allowed.

*2 $PW \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$

*3 Example of acceptable Vgs waveform



*4 Pulsed

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Static drain - source on - state resistance	R _{DS(on)} ^{*4}	V _{GS} = 18V, I _D = 1.1A T _j = 25°C T _j = 125°C	- -	1.15 1.71	1.5 -	Ω
Gate input resistance	R _G	f = 1MHz, open drain	-	64	-	Ω
Transconductance	g _{fs} ^{*4}	V _{DS} = 10V, I _D = 1.1A	-	0.4	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	184	-	pF
Output capacitance	C _{oss}	V _{DS} = 800V	-	16	-	
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	6	-	
Effective output capacitance, energy related	C _{o(er)}	V _{GS} = 0V V _{DS} = 0V to 800V	-	17	-	pF
Turn - on delay time	t _{d(on)} ^{*4}	V _{DD} = 500V, I _D = 1.1A	-	16	-	ns
Rise time	t _r ^{*4}	V _{GS} = 18V/0V	-	21	-	
Turn - off delay time	t _{d(off)} ^{*4}	R _L = 455Ω	-	35	-	
Fall time	t _f ^{*4}	R _G = 0Ω	-	74	-	
Turn - on switching loss	E _{on} ^{*4}	V _{DD} = 800V, I _D = 1.1A V _{GS} = 18V/0V R _G = 0Ω, L = 2mH	-	57	-	μJ
Turn - off switching loss	E _{off} ^{*4}	*E _{on} includes diode reverse recovery	-	32	-	

●Gate Charge characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q _g ^{*4}	V _{DD} = 500V	-	14	-	nC
Gate - Source charge	Q _{gs} ^{*4}	I _D = 1A	-	4	-	
Gate - Drain charge	Q _{gd} ^{*4}	V _{GS} = 18V	-	5	-	
Gate plateau voltage	V _(plateau)	V _{DD} = 500V, I _D = 1A	-	10.5	-	V

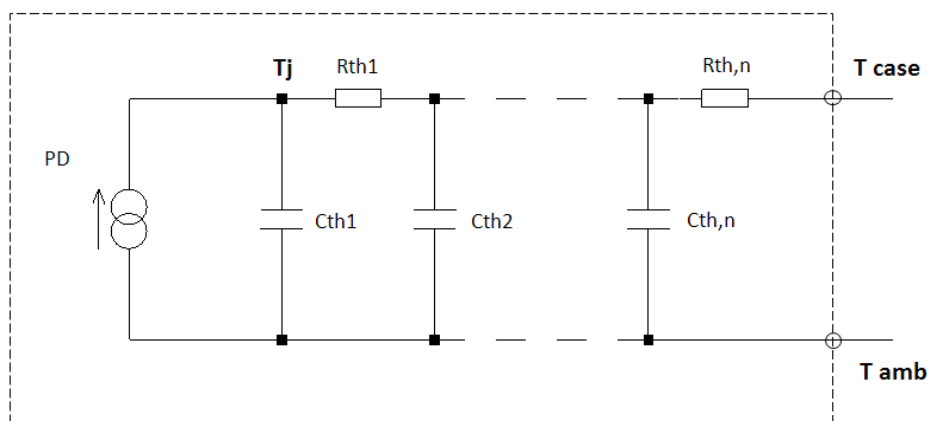
●Body diode electrical characteristics (Source-Drain) ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Inverse diode continuous, forward current	I_S^{*1}	$T_c = 25^\circ\text{C}$	-	-	4	A
Inverse diode direct current, pulsed	I_{SM}^{*2}		-	-	10	A
Forward voltage	V_{SD}^{*4}	$V_{GS} = 0\text{V}, I_S = 1.1\text{A}$	-	4.3	-	V
Reverse recovery time	t_{rr}^{*4}	$I_F = 1.1\text{A}, V_R = 800\text{V}$ $di/dt = 100\text{A}/\mu\text{s}$	-	21	-	ns
Reverse recovery charge	Q_{rr}^{*4}		-	13	-	nC
Peak reverse recovery current	I_{rrm}^{*4}		-	1.1	-	A

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R_{th1}	816m	K/W
R_{th2}	1939m	
R_{th3}	567m	

Symbol	Value	Unit
C_{th1}	127 μ	Ws/K
C_{th2}	1.64m	
C_{th3}	64.5m	



●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

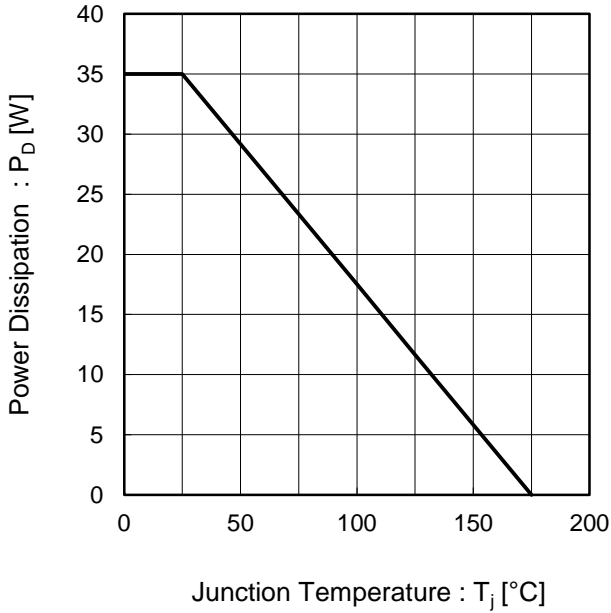


Fig.2 Maximum Safe Operating Area

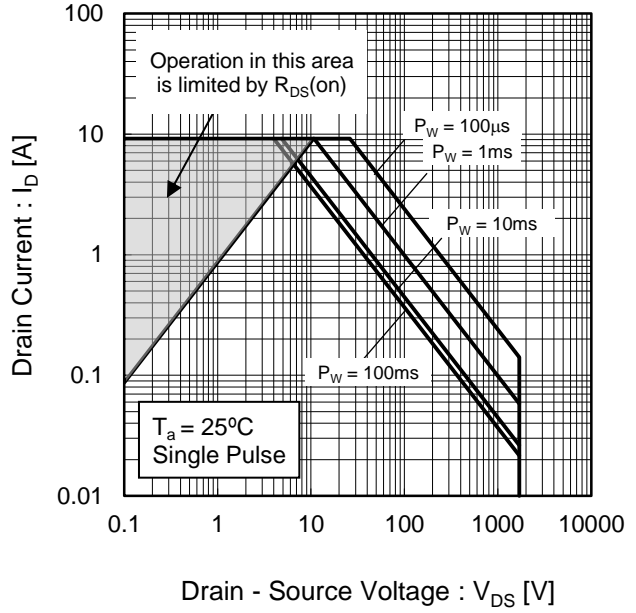
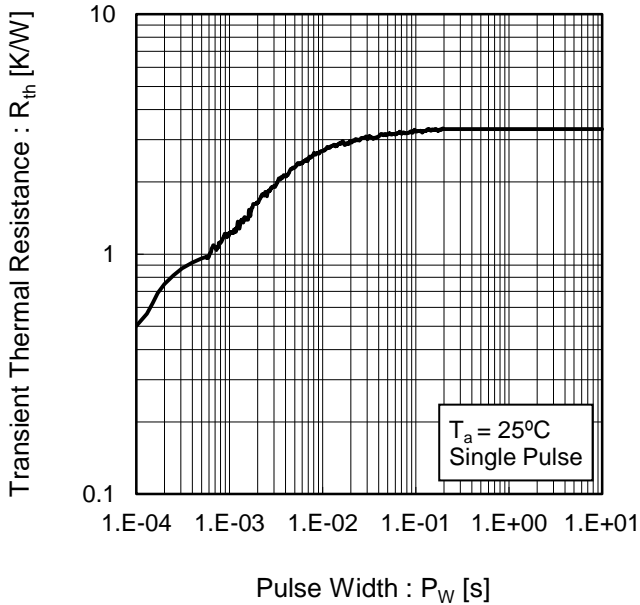


Fig.3 Typical Transient Thermal Resistance vs. Pulse Width



●Electrical characteristic curves

Fig.4 Typical Output Characteristics(I)

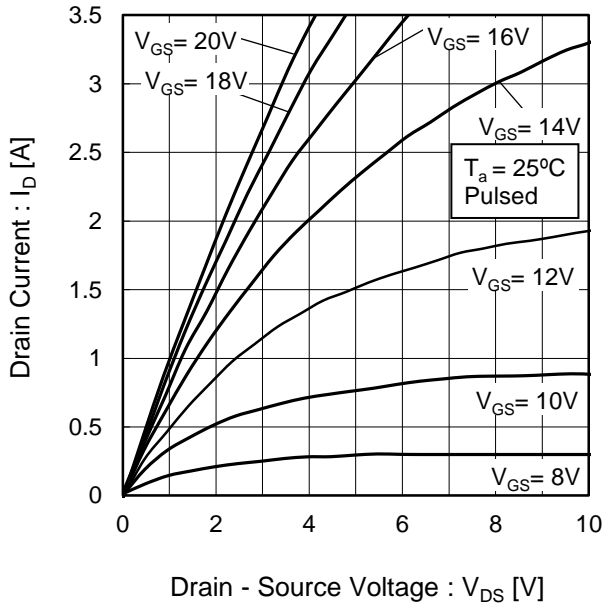


Fig.5 Typical Output Characteristics(II)

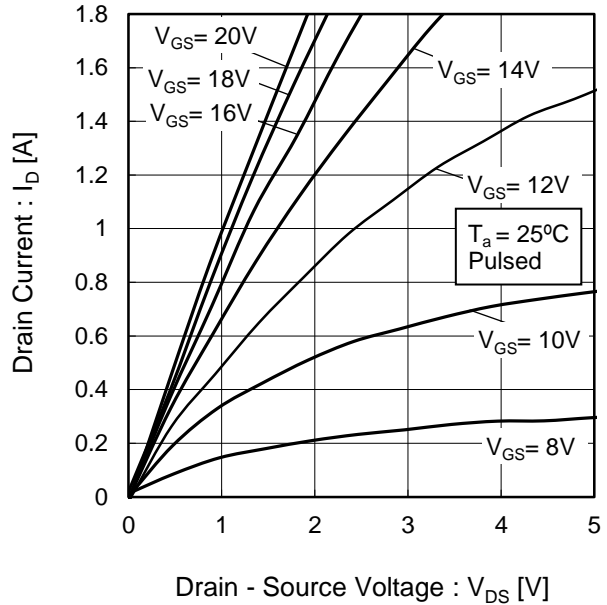


Fig.6 $T_j = 150^\circ\text{C}$ Typical Output Characteristics(I)

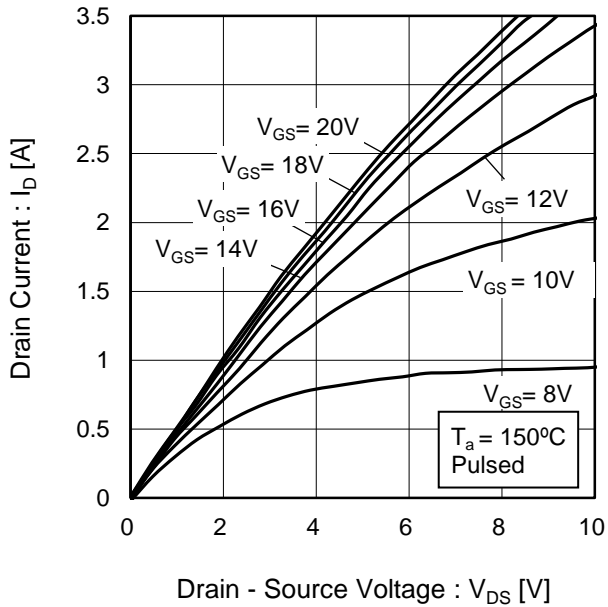
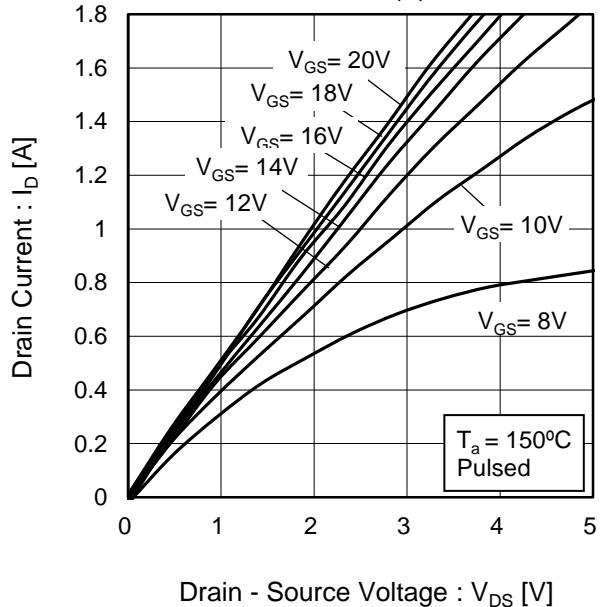


Fig.7 $T_j = 150^\circ\text{C}$ Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.8 Typical Transfer Characteristics (I)

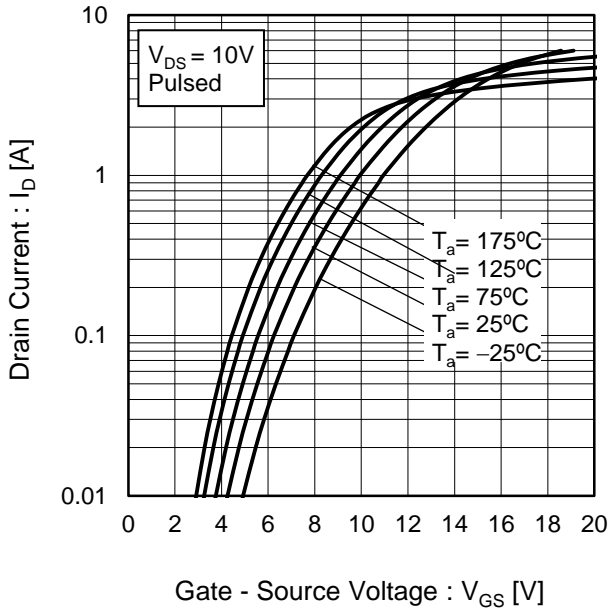


Fig.9 Typical Transfer Characteristics (II)

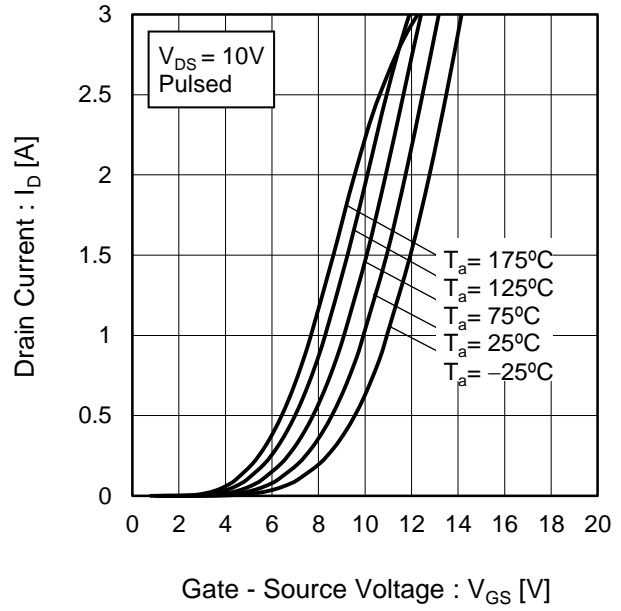


Fig.10 Gate Threshold Voltage vs. Junction Temperature

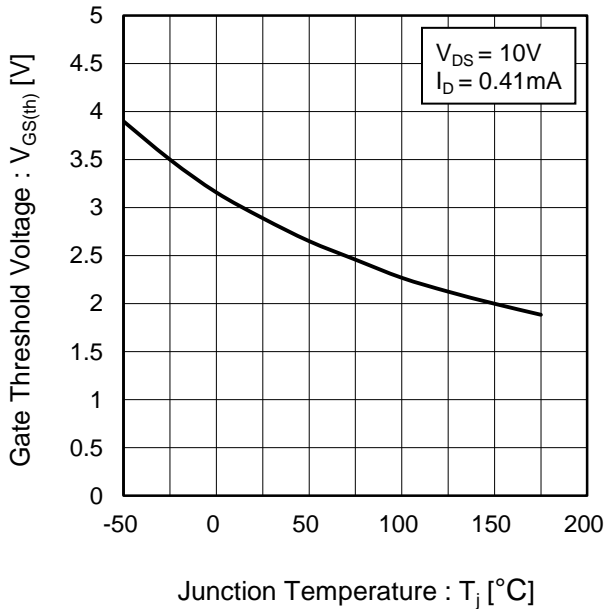
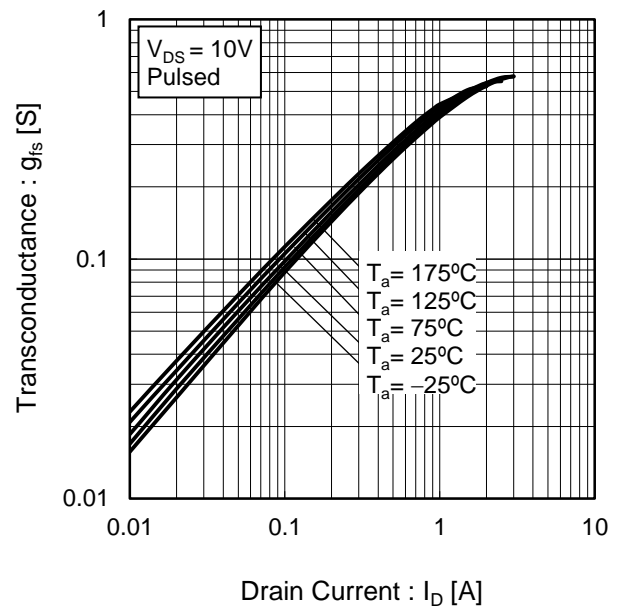


Fig.11 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

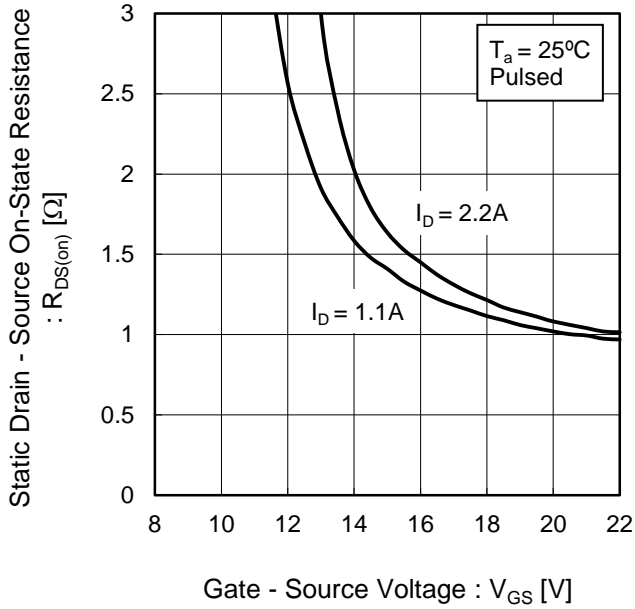


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

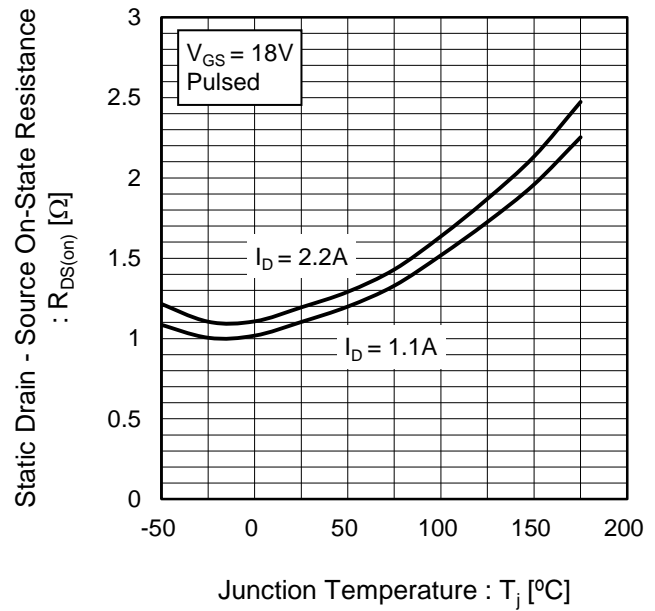
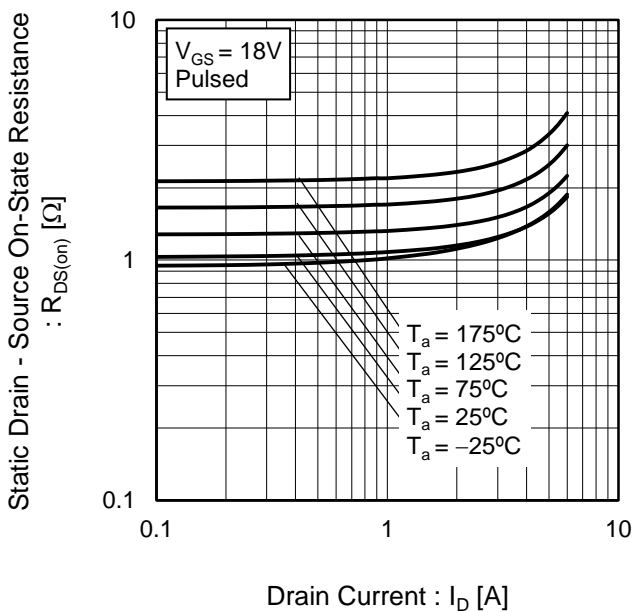


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current



●Electrical characteristic curves

Fig.15 Typical Capacitance vs. Drain - Source Voltage

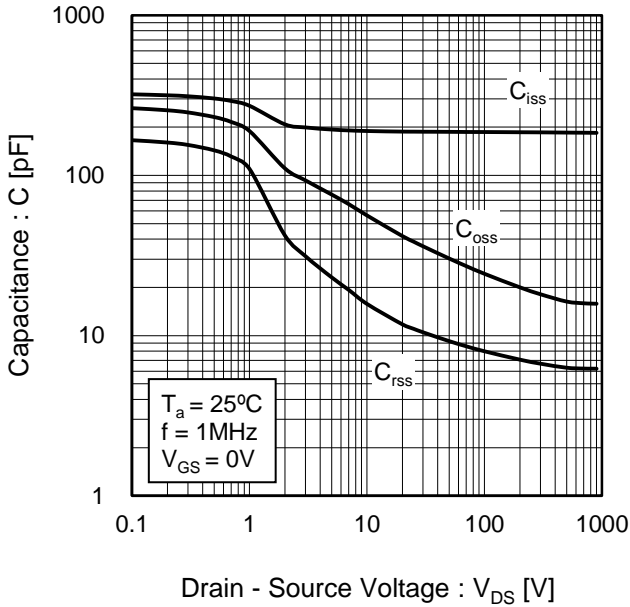


Fig.16 Coss Stored Energy

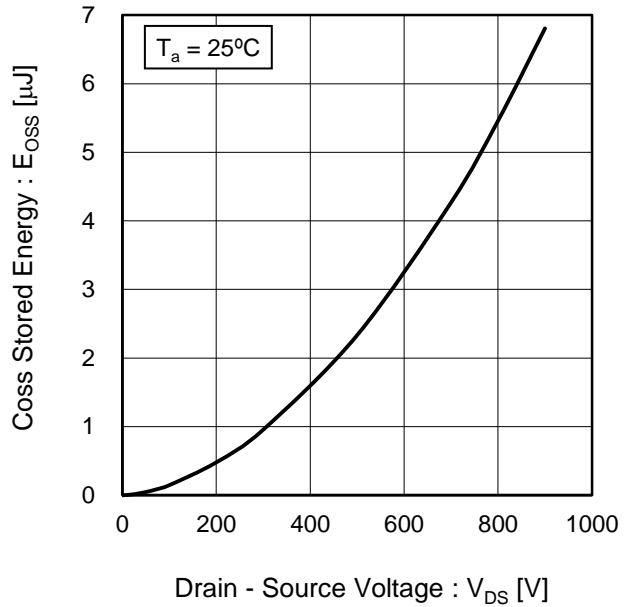


Fig.17 Switching Characteristics

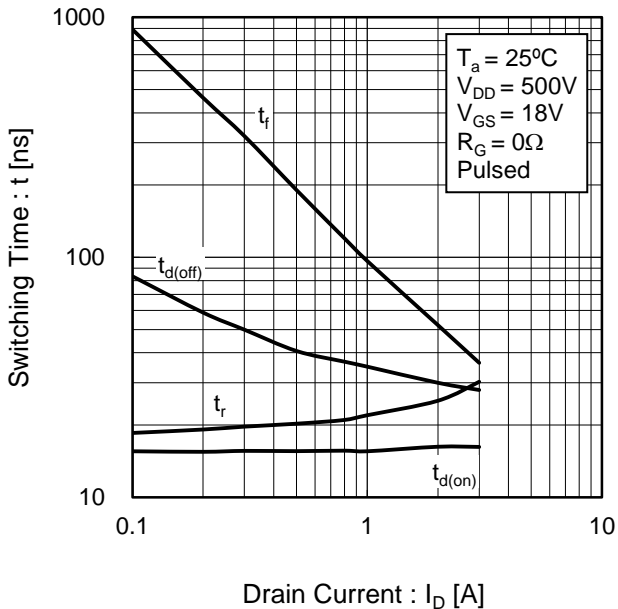
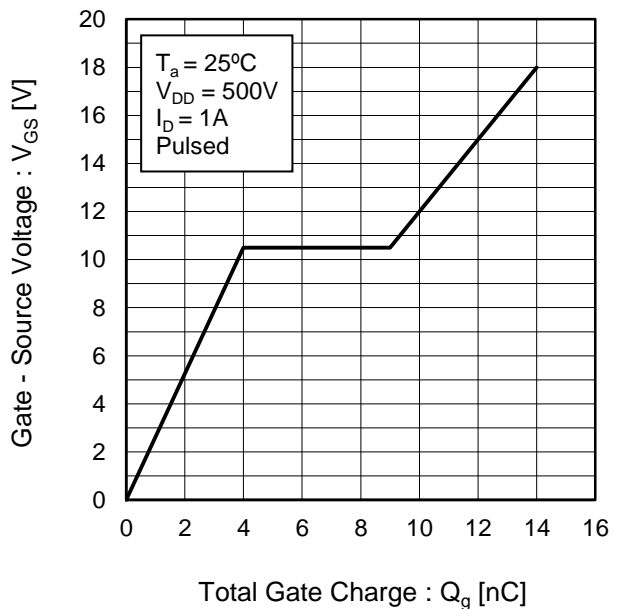


Fig.18 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.19 Typical Switching Loss vs. Drain - Source Voltage

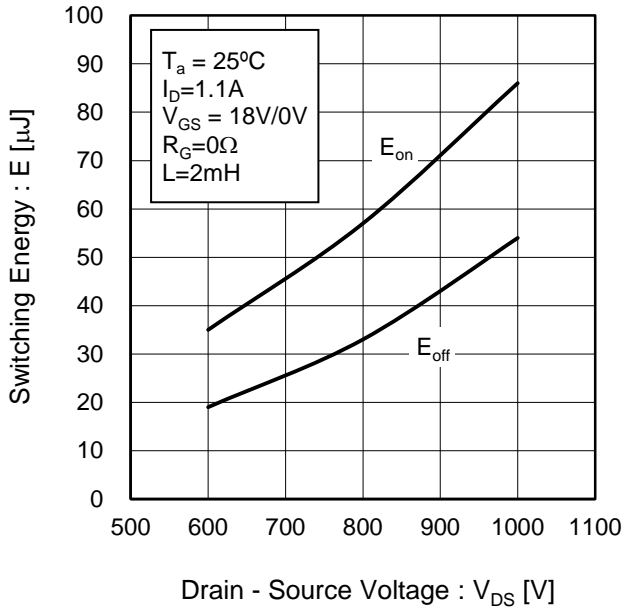


Fig.20 Typical Switching Loss vs. Drain Current

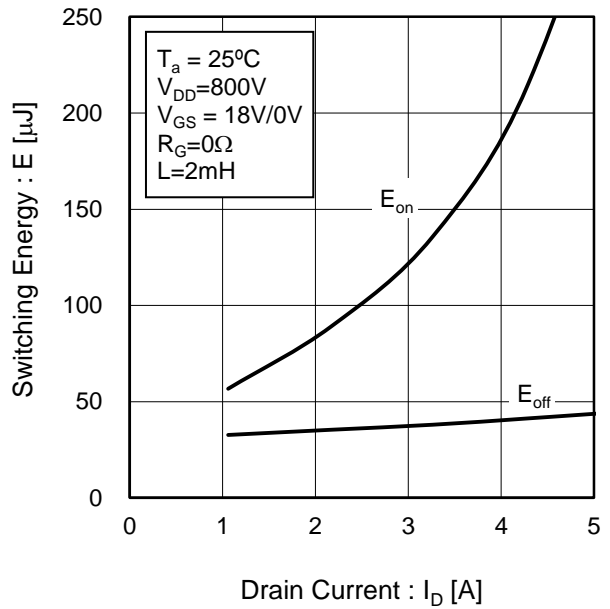
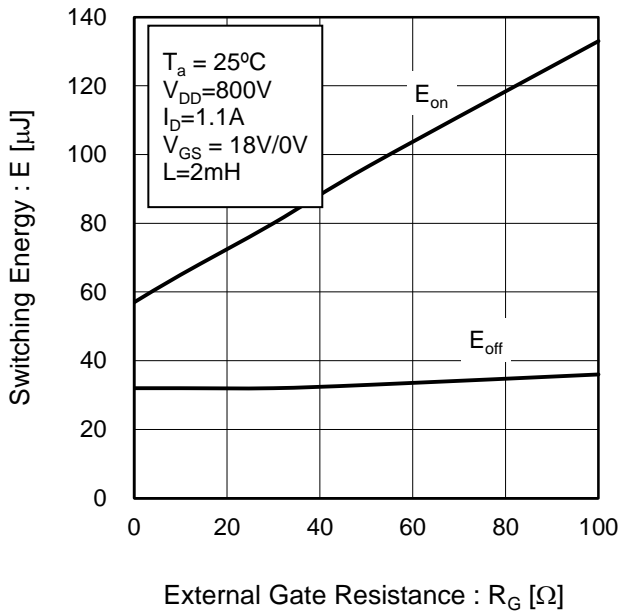


Fig.21 Typical Switching Loss vs. External Gate Resistance



●Electrical characteristic curves

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage

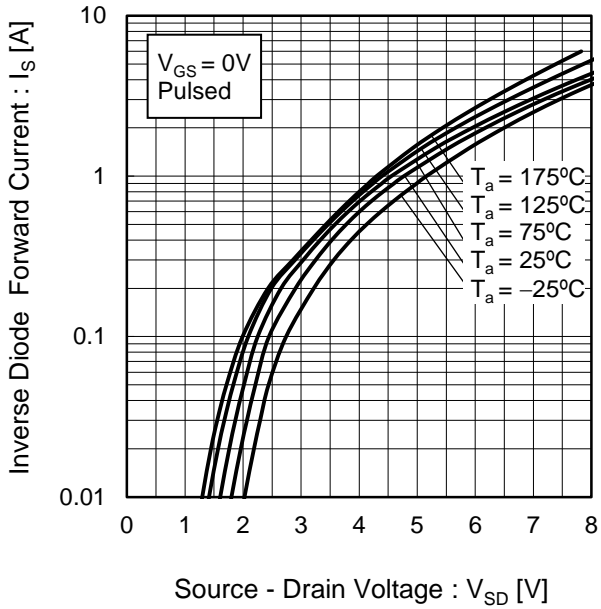
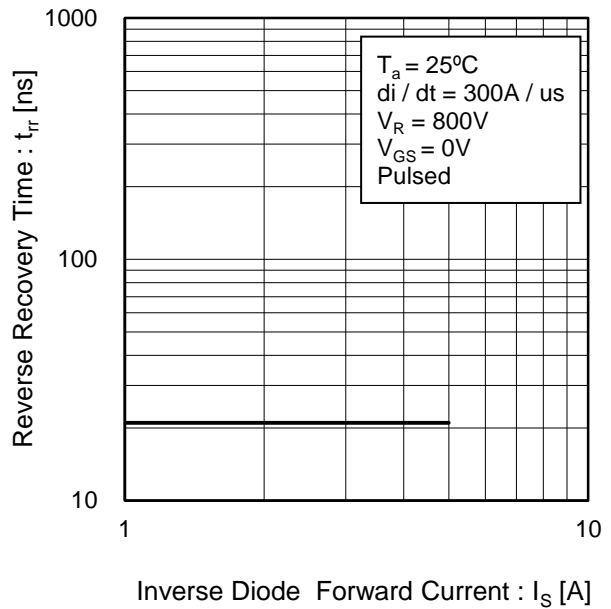


Fig.23 Reverse Recovery Time vs. Inverse Diode Forward Current



● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

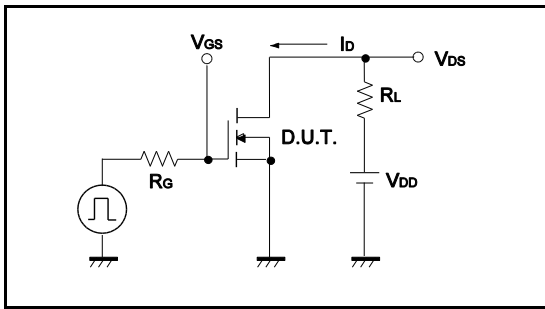


Fig.1-2 Switching Waveforms

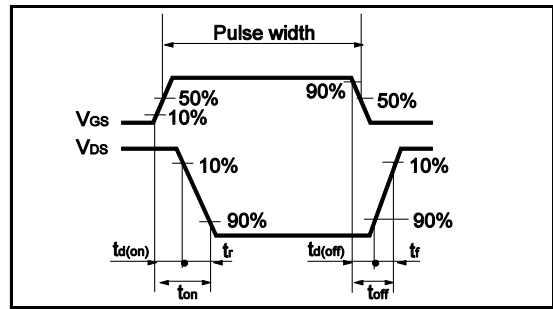


Fig.2-1 Gate Charge Measurement Circuit

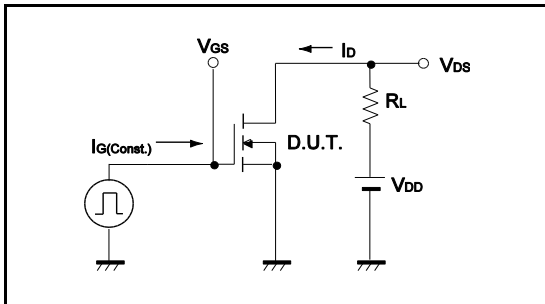


Fig.2-2 Gate Charge Waveform

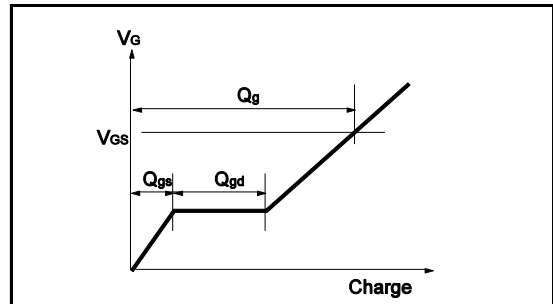


Fig.3-1 Switching Energy Measurement Circuit

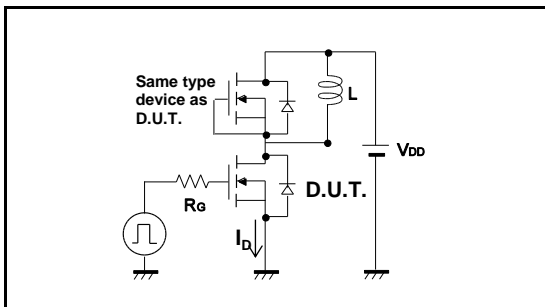


Fig.3-2 Switching Waveforms

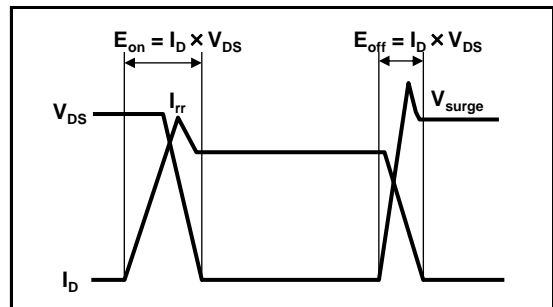


Fig.4-1 Reverse Recovery Time Measurement Circuit

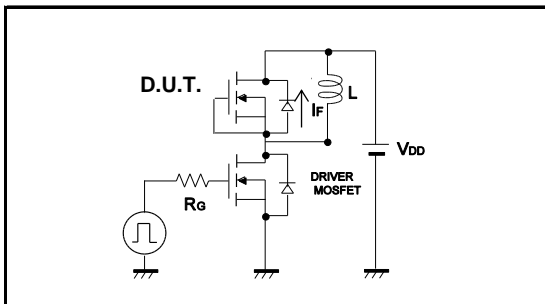
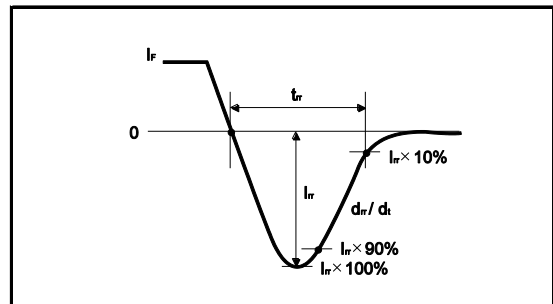
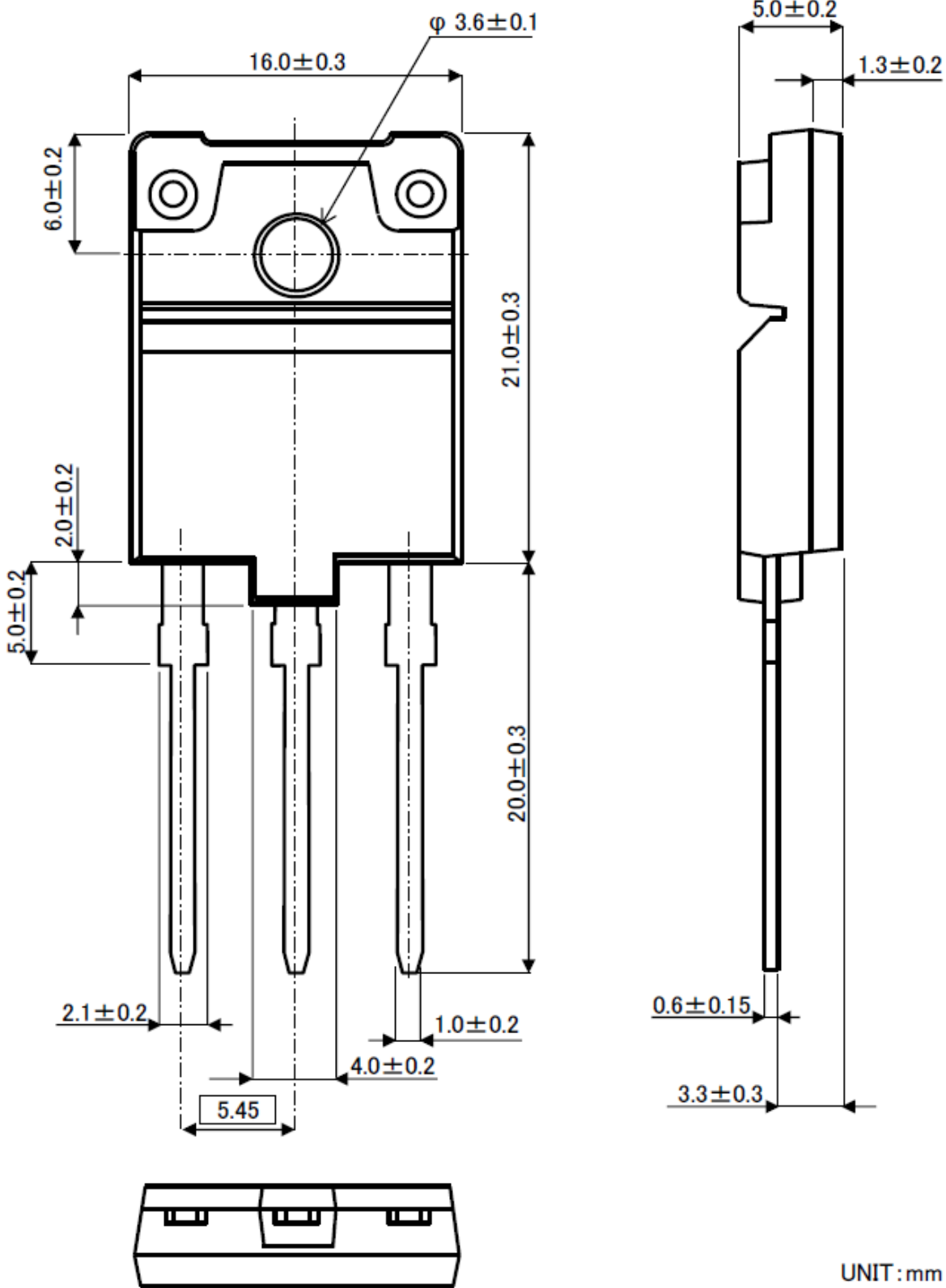


Fig.4-2 Reverse Recovery Waveform



●Dimensions (Unit : mm)

TO-3PFM



UNIT : mm

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